

InP Wafer

n-and p-type InP
Semi-conducting InP Specifications

Fe Doped InP
Semi-insulating GaAs Specifications

TYPE	SC	SI
GROWTH METHOD	VGF	VGF
DOPANT	n-type:S , Sn AND UNDOPED. P-type:Zn	IRON(Fe)
WAFER SHAPE*	ROUND (DIA: 2",3",AND 4")	ROUND (DIA: 2",3",AND 4")
SURFACE ORIENTATION**	(100)±0.5°	(100)±0.5°

*6" WAFERS AVAILABLE UPON REQUEST

**OTHER ORIENTATIONS AND TILT ANGLES AVAILABLE UPON REQUEST

DOPANT	S AND Sn(n-type)	UNDOPED(n-type)	Zn(p-type)	Fe(SI-type)
CARRIER CONCENTRATION (cm ⁻³)	(0.8-8.0)X10 ¹⁸	(1-10)X10 ¹⁵	(0.8-8.0)X10 ¹⁸	
MOBILITY(cm ² /V.s)	(1-2.5)X10 ³	(3-5)X10 ³	50-100	≥1,000
ETCH PITCH DENSITY(cm ⁻²)	100-5,000	≤5,000	≤500	1,500-5,000
RESISTIVITY(Ω .cm)				≥0.5X10 ⁷

WAFER DIAMETER(mm)	50.8±0.3	76.2±0.3	100±0.3	50.8±0.3	76.2±0.3	100±0.3
THICKNESS(μ m)	350±25	625±25	625±25	350±25	625±25	625±25
TTV[P/P](μ m)	≤10	≤10	≤10	≤10	≤10	≤10
TTV[P/E](μ m)	≤10	≤15	≤15	≤10	≤15	≤15
WARP(μ m)	≤15	≤15	≤15	≤15	≤15	≤15
OF(mm)	17±1	22±1	32.5±1	17±1	22±1	32.5±1
OF/IF(mm)	7±1	12±1	18±1	7±1	12±1	18±1
POLISH*	E/E, P/E, P/P	E/E, P/E, P/P	E/E, P/E, P/P	E/E, P/E, P/P	E/E, P/E, P/P	E/E, P/E, P/P

*=ETCHED, P=POLISHED

NOTE: OTHER SPECIFICATIONS AVAILABLE UPON REQUEST

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